

SHANGHAI SUNRISE ELECTRONICS CO., LTD.

M1 THRU M7 SURFACE MOUNT **RECTIFIER**

TECHNICAL SPECIFICATION

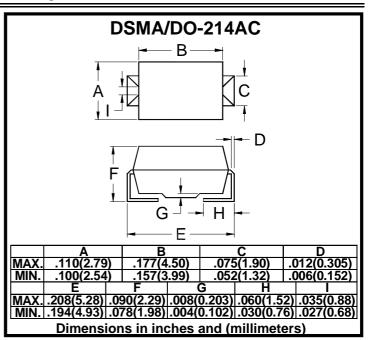
VOLTAGE: 50 TO 1000V CURRENT: 1.0A

FEATURES

- Ideal for surface mount pick and place application
- Low profile package
- Built-in strain relief
- High surge capability
- · Open junction chip, silastic passivated
- High temperature soldering guaranteed: 260°C/10sec/at terminal

MECHANICAL DATA

- Terminal: Plated leads solderable per MIL-STD 202E, method 208C
- Case: Molded with UL-94 Class V-O recognized flame retardant epoxy
- Polarity: Color band denotes cathode



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Single-phase, half-wave, 60Hz, resistive or inductive load rating at 25°C, unless otherwise stated, for capacitive load, derate current by 20%)

RATINGS	SYMBOL	М1	M2	М3	М4	М5	М6	М7	UNITS
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current (T _L =100°C)	I _{F(AV)}	1.0							А
Peak Forward Surge Current (8.3ms single half sine-wave superimposed on rated load)	I _{FSM}	30							А
Maximum Instantaneous Forward Voltage (at rated forward current)	V _F 1.1						V		
Maximum DC Reverse Current T _a =25°C	;	5.0							μΑ
(at rated DC blocking voltage) T _a =125°C	; I _R	200							μΑ
Typical Junction Capacitance (Note 1)	C _J	C _J 15							
Typical Thermal Resistance (Note 2)	$R_{\theta}(ja)$	27							°C/W
Storage and Operation Junction Temperature	T_{STG},T_{J}	-65 to +150							°C

- 1.Measured at 1.0 MHz and applied voltage of 4.0V_{dc}
- 2. Thermal resistance from junction to terminal mounted on 5×5mm copper pad area